Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	316	finfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 14:56
S2	73	S1 and sacrific$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 16:21
S3	243	S1 not S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 16:44
S4	37	S1 and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 16:44
S5	1037	438/585.ccls.	US-PGPUB; USPAT	OR	ON	2005/04/29 17:47
S6	98	438/590.ccls. not (438/585.ccls.)	US-PGPUB; USPAT	OR	ON	2005/04/29 18:20
S7	133	438/183.ccls. not (438/590.ccls. 438/585.ccls.)	US-PGPUB; USPAT	OR	ON	2005/04/29 18:26
S8	229	438/157.ccls. not (438/183.ccls. 438/590.ccls. 438/585.ccls.)	US-PGPUB; USPAT	OR	ON	2005/05/06 17:09
S9	23	S1 and (channel near strain$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 18:46
S10	23	S1 and (aspect adj ratio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 19:17

S11	14	(channel near strain$3) and (((gate structure) near (sacrificial dummy)) with (remov$5 opening))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/30 08:38
S12	1	"6855989"	DERWENT	OR	ON	2005/04/30 12:45
S14	8	(L04-C11C1 and L04-E01B1 and L04-E01C).cpi.	DERWENT	OR	ON	2005/04/30 12:45
S15	14	(sacrificial adj channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/30 13:50
S17	7	"6605498"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/30 13:50
S18	35	((compound adj semiconductor) (silicon adj germanium) SiGe) with channel with sacrificial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 18:11
S19	363	oxide with strain$5 with induc$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 07:48
S20	2	S19 with carbon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 07:42
S21	251	S19 and (oxide with (strain$5 near induc$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 07:49
S22	363	S19 and (oxide near$3 (strain$5 near induc$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 07:49

S23	6	S19 and (oxide near (strain$5 near induc$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:01
S24	580	((compound adj semiconductor) (silicon adj germanium) SiGe) with trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:14
S25	778	((compound adj semiconductor) (silicon adj germanium) SiGe) with (trench aperture)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:03
S26	1	S25 and (strain$5 with (within adj (trench aperture)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:05
S27	4298	((compound adj semiconductor) (silicon adj germanium) SiGe) with (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:17
S28	364	S27 with (improv$7 advantag$5 increas$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:16
S29	25	S28 and (((compound adj semiconductor) (silicon adj germanium) SiGe) near (improv$7 advantag$5 increas$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 08:18
S30	49	finfet and ((source drain) with ((compound adj semiconductor) (silicon adj germanium) SiGe))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:06
S31	180	438/283.ccls. not (438/157.ccls. 438/183.ccls. 438/590.ccls. 438/585.ccls.)	US-PGPUB; USPAT	OR	ON	2005/05/06 17:09